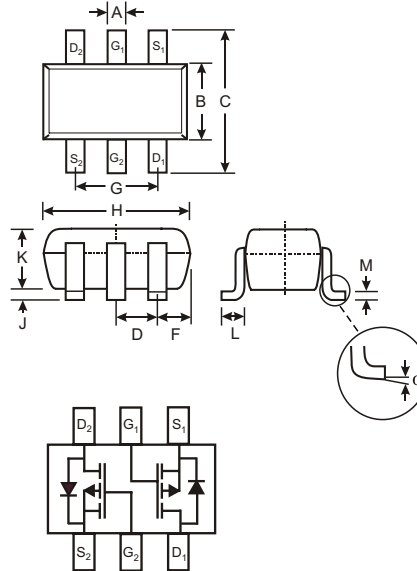


Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Available in Lead Free/RoHS Compliant Version (Note 3)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 6, on Page 2
- Terminal Connections: See Diagram
- Marking Code (See Page 2): K84
- Ordering & Date Code Information: See Page 2
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-50	V
Drain-Gate Voltage (Note 1)	V _{DGR}	-50	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current (Note 2)	I _D	-130	mA
Total Power Dissipation (Note 2)	P _d	300	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Note: 1. R_{GS} ≤ 20KΩ.
 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 3. No purposefully added lead.

Electrical Characteristics @ T_A = 25°C unless otherwise specified

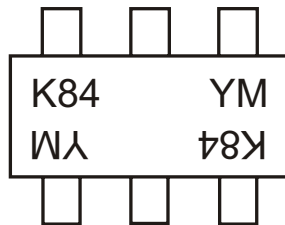
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-15 -60 -100	μA μA nA	V _{DS} = -50V, V _{GS} = 0V, T _J = 25°C V _{DS} = -50V, V _{GS} = 0V, T _J = 125°C V _{DS} = -25V, V _{GS} = 0V, T _J = 25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	-1.6	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6	10	Ω	V _{GS} = -5V, I _D = -0.100A
Forward Transconductance	g _{FS}	0.05	—	—	S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A, R _{GEN} = 50Ω, V _{GS} = -10V
Turn-Off Delay Time	t _{D(OFF)}	—	18	—	ns	

Ordering Information (Note 5)

Device	Packaging	Shipping
BSS84DW-7	SOT-363	3000/Tape & Reel

- Notes:
- Short duration test pulse used to minimize self-heating effect.
 - For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.
 - For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: BSS84DW-7-F.

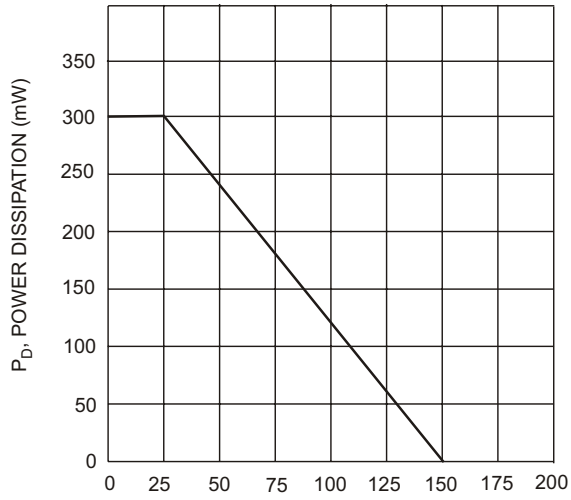
Marking Information



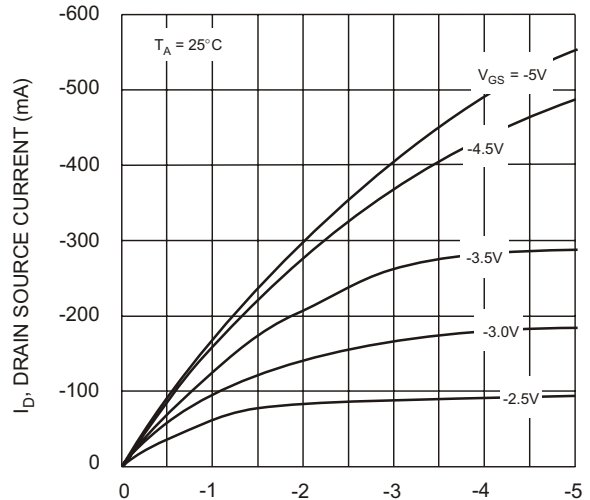
K84 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: N = 2002
 M = Month ex: 9 = September

Date Code Key

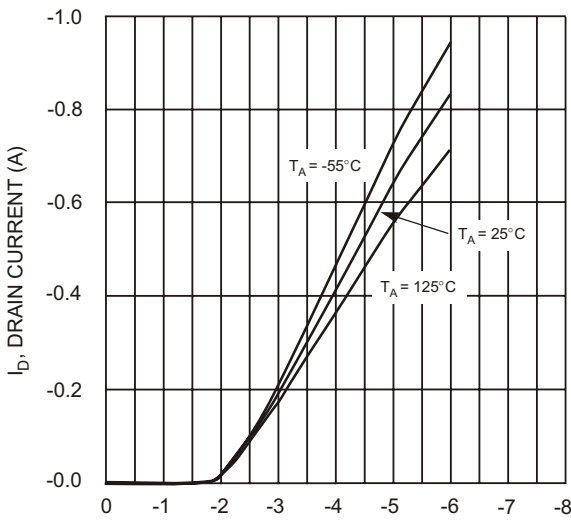
Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009
Code	J	K	L	M	N	P	R	S	T	U	V	W
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



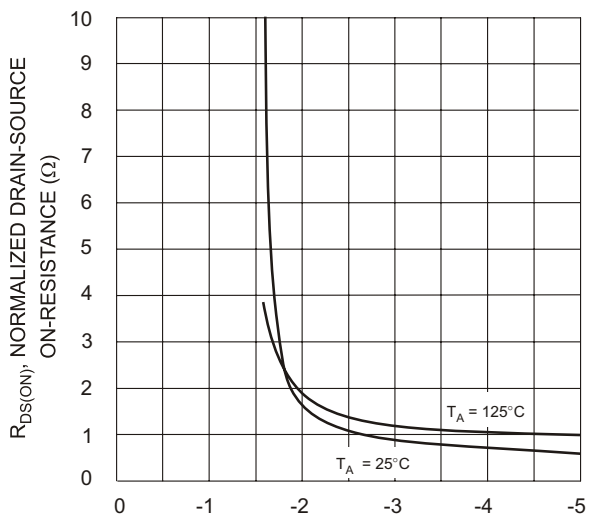
T_A , AMBIENT TEMPERATURE (°C)
Fig. 1, Max Power Dissipation vs Ambient Temperature



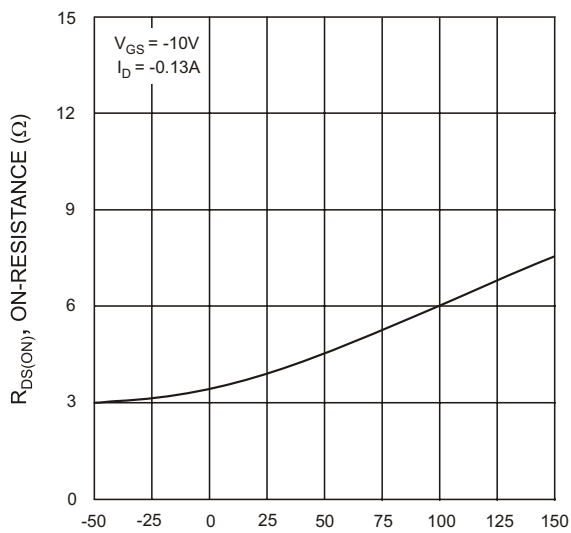
$T_A = 25^\circ\text{C}$
 V_{GS} , DRAIN SOURCE (V)
Fig. 2, Drain Source Current vs. Drain Source Voltage



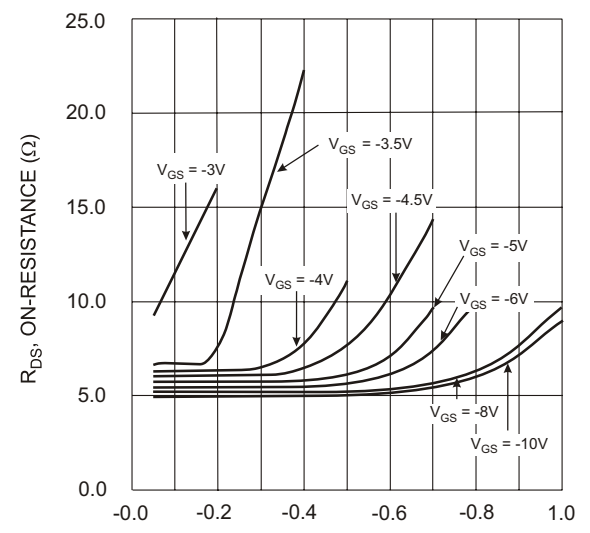
V_{GS} , GATE-TO-SOURCE VOLTAGE (V)
Fig. 3, Drain Current vs. Gate Source Voltage



V_{GS} , GATE TO SOURCE (V)
Fig. 4, On Resistance vs. Gate Source Voltage



T_J , JUNCTION TEMPERATURE (°C)
Fig. 5, On-Resistance vs. Junction Temperature



I_D , DRAIN CURRENT (A)
Fig. 6, On-Resistance vs. Drain Current